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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	37
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100c8t7btr

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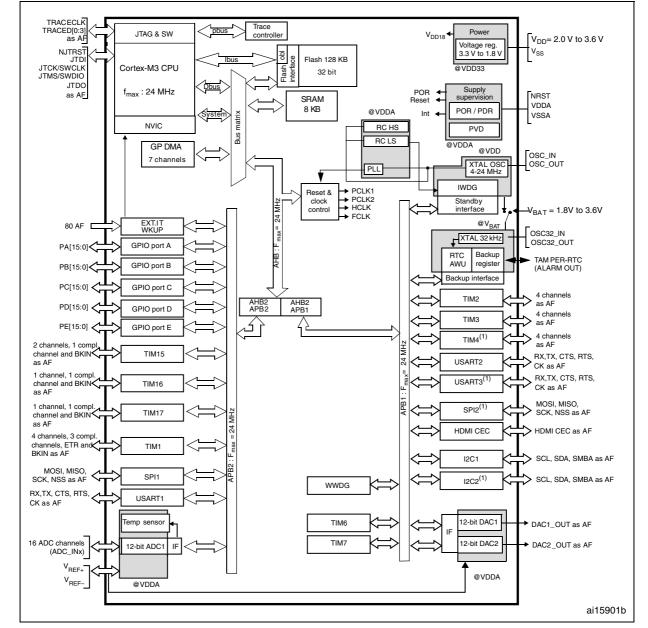


Figure 1. STM32F100xx value line block diagram

- 1. Peripherals not present in low-density value line devices.
- 2. AF = alternate function on I/O port pin.
- 3. $T_A = -40$ °C to +85 °C (junction temperature up to 105 °C) or $T_A = -40$ °C to +105 °C (junction temperature up to 125 °C).

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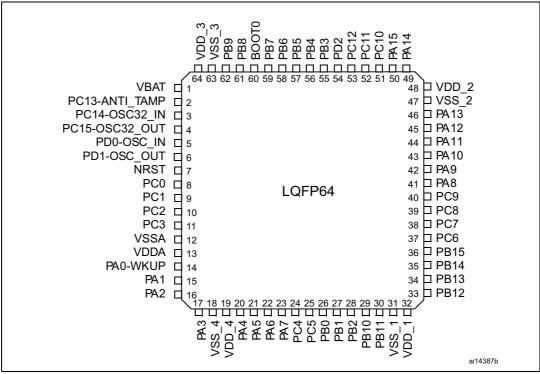
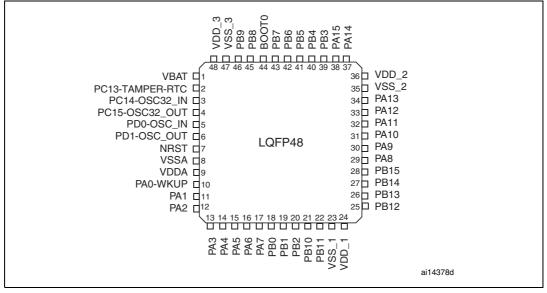


Figure 4. STM32F100xx value line LQFP64 pinout





1 8 PC14-(PC13-) OSC32_INTAMPER RTC PB9 PB3 PA13 PB4 PA15 PA14 PC15-PB8 ВООТО PD2 (PC11) (PC10) В PA12 VBAT, OSC32_OUT (PC12) PB7 ; PB5 (PA10) PA9 С PA11 OSC_OUT PB6 PA8 PC9 D V_{SS_3} VSS_2 VSS_1, V_{DD_4} NRST Ε PC1 PC0 V_{DD_1}, PC7 PC8 $^{V}_{DD_3}$ V_{DD_2} (PB15) PC6; PA5 PC2 PA2 ' PB0 ; 'PB14; F (PB1) PB2 VREF+ PÁ0-WKŲP РАЗ PA6 G PB10 (PB13) Н PC4 PC5 PB11 (PB12) VDDA. Al15494

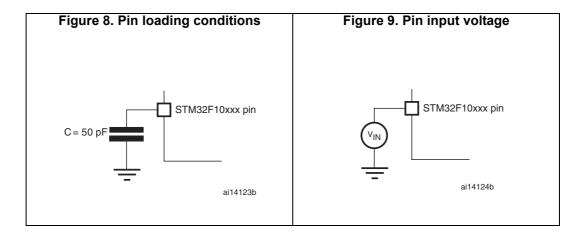
Figure 6. STM32F100xx value line TFBGA64 ballout

Table 4. Low & medium-density STM32F100xx pin definitions

	Pi	ns				2)		Alternate function	s ⁽³⁾⁽⁴⁾
LQFP100	LQFP64	TFBGA64	LQFP48	Pin name	Type ⁽¹⁾	Type (1) Main function (3) (after reset)		Default	Remap
1	-	-	-	PE2	I/O	FT	PE2	TRACECLK	-
2	-	-	-	PE3	I/O	FT	PE3	TRACED0	-
3	-	-	1	PE4	I/O	FT	PE4	TRACED1	-
4	-	-	1	PE5	I/O	FT	PE5	TRACED2	-
5	-	-	-	PE6	I/O	FT	PE6	TRACED3	-
6	1	B2	1	V _{BAT}	S	-	V_{BAT}	-	-
7	2	A2	2	PC13-TAMPER-RTC ⁽⁵⁾	I/O	-	PC13 ⁽⁶⁾	TAMPER-RTC	-
8	3	A1	3	PC14-OSC32_IN ⁽⁵⁾	I/O	-	PC14 ⁽⁶⁾	OSC32_IN	-

- 1. I = input, O = output, S = supply, HiZ= high impedance.
- 2. FT= 5 V tolerant.
- Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripherals that is included. For example, if a device has only one SPI, two USARTs and two timers, they will be called SPI1, USART1 & USART2 and TIM2 & TIM 3, respectively. Refer to Table 2 on page 11.
- 4. If several peripherals share the same I/O pin, to avoid conflict between these alternate functions only one peripheral should be enabled at a time through the peripheral clock enable bit (in the corresponding RCC peripheral clock enable register).
- 5. PC13, PC14 and PC15 are supplied through the power switch and since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is restricted: the speed should not exceed 2 MHz with a maximum load of 30 pF and these IOs must *not* be used as a current source (e.g. to drive an LED).
- 6. Main function after the first backup domain power-up. Later on, it depends on the contents of the Backup registers even after reset (because these registers are not reset by the main reset). For details on how to manage these IOs, refer to the Battery backup domain and BKP register description sections in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.
- 7. The pins number 2 and 3 in the VFQFPN36 package, 5 and 6 in the LQFP48 and LQFP64 packages and C1 and C2 in the TFBGA64 package are configured as OSC_IN/OSC_OUT after reset, however the functionality of PD0 and PD1 can be remapped by software on these pins. For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual.
- 8. Unlike in the LQFP64 package, there is no PC3 in the TFBGA64 package. The V_{REF+} functionality is provided instead.
- 9. I2C2 is not present on low-density value line devices.
- 10. SPI2 is not present on low-density value line devices.
- 11. TIM4 is not present on low-density value line devices.
- 12. This alternate function can be remapped by software to some other port pins (if available on the used package). For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.





5.1.6 **Power supply scheme**

 V_{BAT} Backup circuitry (OSC32K,RTC, Power switch 1.8-3.6V Wake-up logic Backup registers) Ю GP I/Os Logic Kernel logic (CPU, Digital & Memories) V_{DD} 1/2/3/4/5 Regulator 5 × 100 nF V_{SS} + 1 \times 4.7 μ F 1/2/3/4/5 V_{DDA} Analog: 10 nF ADC/DAC V_{REF} RCs, PLL + 1 µF V_{SSA} ai14125e

Figure 10. Power supply scheme

Caution: In Figure 10, the 4.7 μF capacitor must be connected to V_{DD3} .



Symbol Parameter Conditions Min Max Unit LQFP100 434 Power dissipation at T_A = LQFP64 444 P_{D} 85 °C for suffix 6 or T_A = mW TFBGA64 308 105 °C for suffix 7⁽²⁾ LQFP48 _ 363 Maximum power dissipation -4085 Ambient temperature for 6 °C suffix version Low power dissipation⁽³⁾ -40 105 TA Maximum power dissipation -40 105 Ambient temperature for 7 °C suffix version Low power dissipation⁽³⁾ -40 125 6 suffix version -40 105 °C TJ Junction temperature range -40 125 7 suffix version

Table 8. General operating conditions (continued)

Note:

It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.

5.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A.

Table 9. Operating conditions at power-up / power-down

Symbol	Parameter	Min	Max	Unit	
	V _{DD} rise time rate	0	8	µs/V	
t_{VDD}	V _{DD} fall time rate	20	8	μ5/ ν	

5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 10* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*.



^{1.} When the ADC is used, refer to Table 42: ADC characteristics.

^{2.} If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_Jmax (see *Table 6.5: Thermal characteristics on page 89*).

In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_Jmax (see Table 6.5: Thermal characteristics on page 89).

Table 12. Maximum current consumption in Run mode, code with data processing running from Flash

Symbol	Doromotor	Conditions		Ма	Unit	
	Parameter		f _{HCLK}	T _A = 85 °C	T _A = 105 °C	Joint
		External clock ⁽²⁾ , all peripherals enabled	24 MHz	15.4	15.7	
	Supply current in Run mode		16 MHz	11	11.5	
			8 MHz	6.7	6.9	mA
IDD			24 MHz	10.3	10.5	ША
			16 MHz	7.8	8.1	
			8 MHz	5.1	5.3	

- 1. Guaranteed by characterization results.
- 2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 13. Maximum current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions	•	Ma	Unit	
	Parameter		f _{HCLK}	T _A = 85 °C	T _A = 105 °C	
		External clock ⁽²⁾ , all peripherals enabled	24 MHz	14.5	15	
	Supply current in Run mode		16 MHz	10	10.5	mA
			8 MHz	6	6.3	
IDD		External clock ⁽²⁾ all peripherals disabled	24MHz	9.3	9.7	IIIA
			16 MHz	6.8	7.2	
			8 MHz	4.4	4.7	

- 1. Guaranteed by characterization, tested in production at $V_{\mbox{\scriptsize DD}}\,\mbox{\scriptsize max},\,f_{\mbox{\scriptsize HCLK}}\,\mbox{\scriptsize max}.$
- 2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.



Table 15. Typical and maximum current consumptions in Stop and Standby modes

					M			
Symbol	Parameter	Conditions	V _{DD} / V _{BAT} = 2.0 V	V _{DD} / V _{BAT} = 2.4 V	V _{DD} / V _{BAT} = 3.3 V	T _A = 85 °C	T _A = 105 °C	Unit
	Supply current in Stop mode	Regulator in Run mode, Low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	23.5	24	190	350	
		Regulator in Low-Power mode, Low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	13.5	14	170	330	
I _{DD}	Supply current in Standby mode	Low-speed internal RC oscillator and independent watchdog ON	-	2.6	3.4	-	-	μА
		Low-speed internal RC oscillator ON, independent watchdog OFF	-	2.4	3.2	-	-	
		Low-speed internal RC oscillator and independent watchdog OFF, low-speed oscillator and RTC OFF	-	1.7	2	4	5	
I _{DD_VBAT}	Backup domain supply current	Low-speed oscillator and RTC ON	0.9	1.1	1.4	1.9	2.2	

^{1.} Typical values are measured at T_A = 25 °C.

Figure 14. Typical current consumption on $\rm V_{BAT}$ with RTC on vs. temperature at different $\rm V_{BAT}$ values

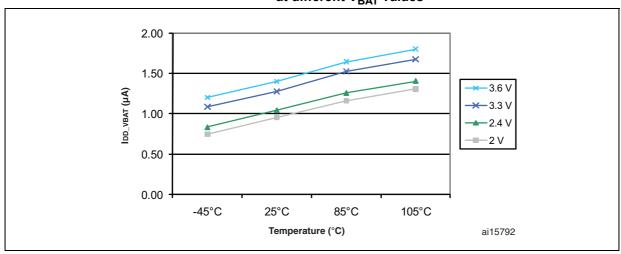


Table 16. Typical current consumption in Run mode, code with data processing running from Flash

				Typical		
Symbol	Parameter	Conditions	f _{HCLK}	All peripherals enabled ⁽²⁾	All peripherals disabled	Unit
			24 MHz	12.8	9.3	
			16 MHz	9.3	6.6	
			8 MHz	5.1	3.9	
		Running on high-speed external clock with an	4 MHz	3.2	2.5	
		8 MHz crystal ⁽³⁾	2 MHz	2.1	1.75	
	Supply current in		1 MHz	1.55	1.4	
			500 kHz	1.3	1.2	
			125 kHz	1.1	1.05	- mA
I _{DD}	Run mode		24 MHz	12.2	8.6	
			16 MHz	8.5	6	
			8 MHz	4.6	3.3	
		Running on high-speed	4 MHz	2.6	1.9	
		internal RC (HSI)	2 MHz	1.5	1.15	
			1 MHz	0.9	0.8	
			500 kHz	0.65	0.6	
			125 kHz	0.45	0.43	

^{1.} Typical values are measures at T_A = 25 °C, V_{DD} = 3.3 V.

^{2.} Add an additional power consumption of 0.8 mA for the ADC and of 0.5 mA for the DAC analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).

^{3.} An 8 MHz crystal is used as the external clock source. The AHB prescaler is used to reduce the frequency when f_{HCLK} < 8 MHz, the PLL is used when f_{HCLK} > 8 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	24	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
C _{L1} C _{L2} ⁽³⁾	Recommended load capacitance versus equivalent serial resistance of the crystal (R _S) ⁽⁴⁾	R _S = 30 Ω	-	30	-	pF
i ₂	HSE driving current	V_{DD} = 3.3 V V_{IN} = V_{SS} with 30 pF load	ı	-	1	mA
9 _m	Oscillator transconductance	Startup	25	-	ı	mA/V
t _{SU(HSE)}	Startup time	V _{DD} is stabilized	-	2	-	ms

Table 21. HSE 4-24 MHz oscillator characteristics⁽¹⁾⁽²⁾

- 1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
- 2. Guaranteed by characterization results.
- 3. It is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.
- 4. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
- t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

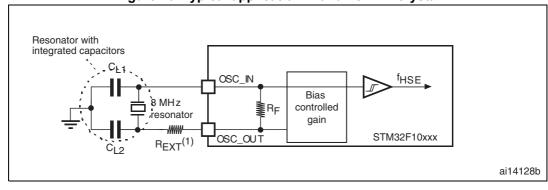


Figure 20. Typical application with an 8 MHz crystal

1. R_{EXT} value depends on the crystal characteristics.



5.3.16 Communications interfaces

I²C interface characteristics

Unless otherwise specified, the parameters given in *Table 39* are derived from tests performed under the ambient temperature, f_{PCLK1} frequency and V_{DD} supply voltage conditions summarized in *Table 8*.

The STM32F100xx value line I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 39*. Refer also to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Table 35. I C Characteristics							
Symbol	Parameter	Standard r	node I ² C ⁽¹⁾	Fast mode	Unit		
Symbol	ratattietei	Min	Max	Min	Max	Unit	
t _{w(SCLL)}	SCL clock low time	4.7	-	1.3	-	110	
t _{w(SCLH)}	SCL clock high time	4.0	-	0.6	-	μs	
t _{su(SDA)}	SDA setup time	250	-	100	-		
t _{h(SDA)}	SDA data hold time	0	-	0	900 ⁽³⁾		
$t_{r(SDA)} \ t_{r(SCL)}$			-	300	ns		
t _{f(SDA)}	SDA and SCL fall time	-	300	-	300	300	
t _{h(STA)}	Start condition hold time	4.0	-	0.6	-		
t _{su(STA)}	Repeated Start condition setup time	4.7	-	0.6	-	μs	
t _{su(STO)}	Stop condition setup time	4.0	-	0.6	-	μs	
t _{w(STO:STA)}	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs	
C _b	Capacitive load for each bus line	-	400	-	400	pF	

Table 39, I²C characteristics

^{1.} Guaranteed by design.

f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I2C fast mode clock.

The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

Table 42. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V _{REF+}	Positive reference voltage	-	2.4	-	V_{DDA}	V
I _{VREF}	Current on the V _{REF} input pin	-	-	160 ⁽¹⁾	220 ⁽¹⁾	μΑ
f _{ADC}	ADC clock frequency	-	0.6	-	12	MHz
f _S ⁽²⁾	Sampling rate	-	0.05	-	1	MHz
£ (2)	E 1	f _{ADC} = 12 MHz	-	-	705	kHz
f _{TRIG} ⁽²⁾	External trigger frequency	-	-	-	17	1/f _{ADC}
V _{AIN} ⁽³⁾	Conversion voltage range	-	0 (V _{SSA} tied to ground)	-	V _{REF+}	V
R _{AIN} ⁽²⁾	External input impedance	See Equation 1 and Table 43 for details	-	-	50	κΩ
R _{ADC} ⁽²⁾	Sampling switch resistance	-	-	-	1	κΩ
C _{ADC} ⁽²⁾	Internal sample and hold capacitor	-	-	-	8	pF
t _{CAL} ⁽²⁾	Calibration time	f _{ADC} = 12 MHz	6.9		μs	
rCAL, ,	Calibration time	-	83		1/f _{ADC}	
. (2)	Injection trigger conversion	f _{ADC} = 12 MHz	-	-	0.25	μs
t _{lat} ⁽²⁾	latency	-	-	-	3 ⁽⁴⁾	1/f _{ADC}
t _{latr} ⁽²⁾	Regular trigger conversion	f _{ADC} = 12 MHz	-	-	0.166	μs
latr'	latency	-	-	-	2 ⁽⁴⁾	1/f _{ADC}
t _S ⁽²⁾	Compaling times	f _ 40 MH=	0.125	-	20.0	μs
	Sampling time	f_{ADC} = 12 MHz	1.5	-	239.5	1/f _{ADC}
t _{STAB} ⁽²⁾	Power-up time	-	0	0	1	μs
	Tatal aggregation times	f _{ADC} = 12 MHz	1.17	-	21	μs
t _{CONV} ⁽²⁾	Total conversion time (including sampling time)	14 to 252 (t _S for sampling +12.5 for successive approximation)			1/f _{ADC}	

- 1. Based on characterization results, not tested in production.
- Guaranteed by design.
- V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA} , depending on the package. Refer to *Table 4: Low & medium-density STM32F100xx pin definitions* and *Figure 6* for further details.
- 4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 42*.

Equation 1:
$$R_{AIN}$$
 max formula: T_S

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times ln(2^{N+2})} - R_{ADC}$$

The above formula (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).



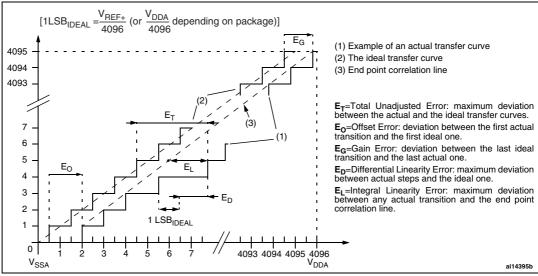
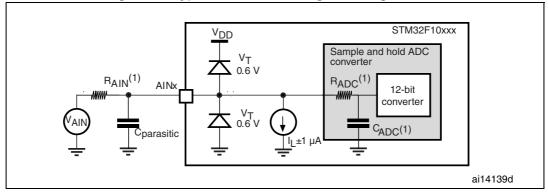


Figure 32. ADC accuracy characteristics





- 1. Refer to *Table 42* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
- C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C_{parasitic} value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 34* or *Figure 35*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.



Symbol	Parameter	Min	Тур	Max ⁽¹⁾	Unit	Comments
	Offset error (difference between measured value at Code (0x800) and the ideal value = V _{REF+} /2)	-	-	±10	mV	Given for the DAC in 12-bit configuration
Offset ⁽¹⁾		-	-	±3	LSB	Given for the DAC in 10-bit at V _{REF+} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V _{REF+} = 3.6 V
Gain error ⁽¹⁾	Gain error	-	-	±0.5	%	Given for the DAC in 12bit configuration
t _{SETTLING} ⁽¹⁾	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	μs	$C_{LOAD} \le 50 \text{ pF, } R_{LOAD} \ge 5 \text{ k}\Omega$
Update rate ⁽¹⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	ı	ı	1	MS/s	$C_{LOAD} \le 50 \text{ pF, } R_{LOAD} \ge 5 \text{ k}\Omega$
t _{WAKEUP} (1)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	μs	$C_{LOAD} \le 50$ pF, $R_{LOAD} \ge 5$ k Ω input code between lowest and highest possible ones.
PSRR+ (1)	Power supply rejection ratio (to V_{DDA}) (static DC measurement	-	– 67	-40	dB	No R _{LOAD} , C _{LOAD} = 50 pF

Table 46. DAC characteristics (continued)

- Guaranteed by characterization results.
- 2. Guaranteed by design.

Buffer(1)

Figure 36. 12-bit buffered /non-buffered DAC

Buffered/Non-buffered DAC R_L 12-bit digital to analog DAC_OUTx converter C_L ai17157V2

The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

Table 48. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Compleal	millimeters			inches ⁽¹⁾			
Symbol	Min	Тур	Max	Min	Тур	Max	
А	-	-	1.600	-	-	0.0630	
A1	0.050	-	0.150	0.0020	-	0.0059	
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571	
b	0.170	0.220	0.270	0.0067	0.0087	0.0106	
С	0.090	-	0.200	0.0035	-	0.0079	
D	15.800	16.000	16.200	0.6220	0.6299	0.6378	
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591	
D3	-	12.000	-	-	0.4724	-	
E	15.800	16.000	16.200	0.6220	0.6299	0.6378	
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591	
E3	-	12.000	-	-	0.4724	-	
е	-	0.500	-	-	0.0197	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°	
ccc	-	-	0.080	-	-	0.0031	

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.



Table 55. Document revision history (continued)

Date	Revision	Changes
08-Jun-2012	7	Updated Table 6: Current characteristics on page 34 Updated Table 39: I2C characteristics on page 64 Corrected note "non-robust" in Section 5.3.17: 12-bit ADC characteristics on page 68 Updated Section 5.3.13: I/O port characteristics on page 57 Updated Section 2.2.20: GPIOs (general-purpose inputs/outputs) on page 20 Updated Table 4: Low & medium-density STM32F100xx pin definitions on page 24 Updated Section 5.3.1: General operating conditions on page 34 Updated Table 14: Maximum current consumption in Sleep mode, code running from Flash or RAM on page 39
08-Jun-2015	8	Updated Table 18: Peripheral current consumption, Table 31: ESD absolute maximum ratings, Table 48: LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data, Table 49: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data, Table 50: TFBGA64 - 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data, Table 51: TFBGA64 recommended PCB design rules (0.5 mm pitch BGA) and Table 52: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data. Updated Figure 37: LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline, Figure 38: LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint, Figure 40: LQFP64 - 10 x 10 mm 64 pin low-profile quad flat package outline, Figure 41: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint, Figure 43: TFBGA64 - 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline, Figure 44: TFBGA64 - 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array, recommended footprint, Figure 46: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline and Figure 47: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package recommended footprint. Added Figure 39: LQFP100 marking example (package top view) Figure 45: TFBGA64 marking example (package top view) and Figure 48: LQFP48 marking example (package top view).
21-Nov-2016	9	Updated: - Figure 7: Memory map - Figure 18: High-speed external clock source AC timing diagram - Figure 19: Low-speed external clock source AC timing diagram - Table 19: High-speed external user clock characteristics - Table 20: Low-speed external user clock characteristics - Table 42: ADC characteristics



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